IN THE SPECIFICATION:

Please replace the paragraph bridging pages 14 and 15, which starts " Additionally" with the following:

Additionally, when an organic thin-film transistor having an organic semiconductor layer made of tetradecafluoropentacene as a fluorinated acene compound is fabricated, the organic semiconductor layer is formed, preferably, by controlling the temperature of a substrate for the organic thin-film transistor to 30 °C or higher and 65 °C or lower and vacuum-depositing tetradecafluoropentacene on the substrate. Herein, to vacuum-deposit ~~tetrafluoropentacene~~ tetradecafluoropentacene on a substrate includes both to directly vacuum-deposit ~~tetrafluoropentacene~~ tetradecafluoropentacene on a surface of a substrate so as to directly form a thin film of ~~tetrafluoropentacene~~ tetradecafluoropentacene on the surface of the substrate and to from another layer on a surface of a substrate and subsequently vacuum-deposit ~~tetrafluoropentacene~~ tetradecafluoropentacene on a surface of the another layer formed on the substrate so as to form a thin film of ~~tetrafluoropentacene~~ tetradecafluoropentacene on the surface of the another layer formed on the substrate. Thus, an organic semiconductor layer in which plural molecules of tetradecafluoropentacene are comparatively uniformly oriented can be obtained by controlling the temperature of a substrate for an organic thin-film transistor to 30 °C or higher and 65 °C or lower and vacuum-depositing tetradecafluoropentacene on the substrate so that an organic semiconductor

layer made of tetradecafluoropentacene is formed. Also, in this case, molecular planes of plural molecules of tetradecafluoropentacene are approximately parallel to each other and a longer axis of the molecule of tetradecafluoropentacene is directed to directions which are approximately perpendicular to a surface of a substrate for an organic thin-film transistor. Therefore, an organic thin-film transistor having a high carrier-mobility can be fabricated.

Please replace the paragraph bridging pages 42 and 43, which starts "Melting" with the following:

Melting point: 179 – 183 °C

^{19}F NMR (188 MHz, solvent: $CDCl_3$, reference material: C_6F_6)

δ 71.90 - 71.78 (m, 8F), 25.64 - 25.44 (m, 4F), 16.30 (d, J=12.4 Hz, 4F)

Mass spectrometry (MS m/z): 520 (M^+, 93), 501 (M^+ - F, 40), 451 (M^+ - CF_3, 100), 432 (29), 413 (47.2), 401 (43), 382 (80)

Elemental analysis

Calculated values for $C_{18}F_{16}$: C, 41.56

Found values: C, 41.22

{1 – 2 - 2} Further to {1 - 1}, 1,2,3,4,5,5,6,6,7,8,9,10,11,11,12,12-hexadecafluoro-5,6,11,12-tetrahydronaphthacene (8) and ~~1,2,3,4,5,5,6,6,7,8,9,10,11,11,12,12-hexadecafluoro-5,6,11,12-~~

~~tetrahydronaphthacene~~ 1,2,3,4,5,5,6,7,8,9,10,11,12,12-tetradecafluoro-5,12-dihydronaphthacene (9) were synthesized from the obtained 1,2,3,4,7,8,9,10-octafluoro-6,11-dihydroxynaphthacene-5,12-dione (7).